

## 12500 TI Boulevard, MS 8640, Dallas, Texas 75243

# PCN# 20191104001.1 Conversion to TSMC 0.6/0.5um Hybrid Process Change Notification / Sample Request

**Date:** November 22, 2019 **To:** PREMIER FARNELL PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

Texas Instruments requires acknowledgement of receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If samples or additional data are required, requests must be received within **30 days** of this notification.

The changes discussed within this PCN will not take effect any earlier than the proposed first ship date on Page 3 of this notification, unless customer agreement has been reached on an earlier implementation of the change.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the PCN Team (<a href="mailto:PCN\_www\_admin\_team@list.ti.com">PCN\_www\_admin\_team@list.ti.com</a>). For sample requests or sample related questions, contact your local Field Sales Representative.

PCN Team SC Business Services

# 20191104001.1 Attachment: 1

# **Products Affected:**

The devices listed on this page are a subset of the complete list of affected devices. According to our records, these are the devices that you have purchased within the past twenty-four (24) months. The corresponding customer part number is also listed, if available.

DEVICE	<b>CUSTOMER PART NUMBER</b>
REF3130AIDBZTG4	null
REF3112AIDBZT	null
REF3120AIDBZT	null
REF3125AIDBZT	null
REF3130AIDBZR	null
REF3130AIDBZT	null
REF3133AIDBZT	null
REF3140AIDBZT	null
REF3212AIDBVT	null
REF3220AIDBVT	null
REF3225AIDBVR	null
REF3225AIDBVT	null
REF3230AIDBVT	null
REF3233AIDBVT	null
REF3240AIDBVT	null
REF3125AIDBZR	null

Technical details of this Product Change follow on the next page(s).

PCN Number: 20			20191104001.1					l Da	ite:	Nov 13, 2019			
Title:	Conversion t	to TSMC	SMC 0.6/0.5um Hybrid Process										
Custom	ner Contact:	<u> </u>	PCN Manager				Dep	t:		Quality Services			
Propos	ed 1 <sup>st</sup> Ship Date	e: F	Feb 13, 2020			Estimated Sample Availability:				Date provided at sample request.			
Change	е Туре:												
	sembly Site		Assembly Process Assembly Materials										
	esign		Electrical Specification					<u> </u>		anical Specification			
	st Site afer Bump Site		Packing/Shipping/Labeling					$\mathbf{H}$	Test Process Wafer Bump Process				
	afer Fab Site		Wafer Bump Material Wafer Fab Materials					$\frac{\sqcup}{\boxtimes}$					
	arer rab Site	<u> </u>	Part number change						Ware	1 1 4 1 1 1 0 0 0 0 0 0			
				Notificatio									
Descrip	tion of Change:												
metalliz	ange notification i ation/SOG Etch B I devices listed in	Back prod	cess	to the TSMC	0.5ur	n Tungs	curre ten p	ent lug	TSMC ( back e	0.6um back end end process for the			
	Chang	ge From	n					Ch	ange '	Го			
	0.6um TSMC B									end Process			
	IMD layer: PEOX				I					D-OX+PEOX+SOG			
	Metal: Ti /	AlSiCu	/ []	N						:k+PEOX CVD/AlCu /TiN			
Reason	for Change:				<u> </u>			9	,				
	Improvement.												
	•	Fit, For	orm, Function, Quality or Reliability (positive / negative):										
None.	-	•	-						-	· · · · · · · · · · · · · · · · · · ·			
Change	es to product ide	entifica	tior	resulting fr	om t	his noti	ficat	ion					
None.													
Produc	t Affected:												
REF311													
DEE211	2AIDBZR	REF313	OAI	OBZR	REF3	140TDD1			REF	3225AIDBVTG4			
KEL2II	2AIDBZR 2AIDBZRG4	REF313				140TDD1 140TDD2				3225AIDBVTG4 3230AIDBVR			
			OAII	DBZRG4	REF3				REF				
REF311	2AIDBZRG4	REF313	OAII	DBZRG4 DBZT	REF3	140TDD2	/R		REF REF	3230AIDBVR			
REF311 REF311	2AIDBZRG4 2AIDBZT	REF313	IAO IIAO	DBZRG4 DBZT DBZTG4	REF3 REF3	140TDD2 212AIDB\	/R /T		REF REF	3230AIDBVR 3230AIDBVT			
REF311 REF311 REF312	2AIDBZRG4 2AIDBZT 2AIDBZTG4	REF313 REF313 REF313	IAO IAO IAO	DBZRG4 DBZT DBZTG4 DBZR	REF3 REF3 REF3	140TDD2 212AIDB\ 212AIDB\	/R /T /TG4		REF REF REF	3230AIDBVR 3230AIDBVT 3230AIDBVTG4			
REF311 REF311 REF312 REF312	2AIDBZRG4 2AIDBZT 2AIDBZTG4 0AIDBZR	REF313 REF313 REF313	OAII OAII OAII SAII	DBZRG4 DBZT DBZTG4 DBZR DBZT	REF3 REF3 REF3 REF3	140TDD2 212AIDB\ 212AIDB\ 212AIDB\	/R /T /TG4 /R		REF REF REF REF	3230AIDBVR 3230AIDBVT 3230AIDBVTG4 3233AIDBVR			
REF311 REF311 REF312 REF312	2AIDBZRG4 2AIDBZT 2AIDBZTG4 0AIDBZR 0AIDBZRG4	REF313 REF313 REF313 REF313	IAO IIAO IIAE IIAE	DBZRG4 DBZT DBZTG4 DBZR DBZT DBZTG4	REF3 REF3 REF3 REF3 REF3	140TDD2 212AIDB' 212AIDB' 212AIDB' 220AIDB'	/R /T /TG4 /R /T		REF REF REF REF	3230AIDBVR 3230AIDBVT 3230AIDBVTG4 3233AIDBVR 3233AIDBVT			
REF311 REF311 REF312 REF312 REF312	2AIDBZRG4 2AIDBZT 2AIDBZTG4 0AIDBZR 0AIDBZRG4 0AIDBZRG4	REF313 REF313 REF313 REF313 REF313	OAII OAII OAII OAII OAII OAII OAII OAII	DBZRG4 DBZT DBZTG4 DBZR DBZT DBZT DBZT DBZT DBZTG4 DBZTG4 DBZR	REF3 REF3 REF3 REF3 REF3 REF3	140TDD2 212AIDB\ 212AIDB\ 212AIDB\ 212AIDB\ 220AIDB\	/R /T /TG4 /R /T /TG4		REF REF REF REF REF	3230AIDBVR 3230AIDBVT 3230AIDBVTG4 3233AIDBVR 3233AIDBVT			
REF311 REF312 REF312 REF312 REF312 REF312	2AIDBZRG4 2AIDBZT 2AIDBZTG4 0AIDBZR 0AIDBZRG4 0AIDBZTG4 0AIDBZT	REF313 REF313 REF313 REF313 REF313 REF314	OAII OAII OAII SAII SAII SAII SAII OAII	DBZRG4 DBZT DBZTG4 DBZR DBZT DBZTG4 DBZTG4 DBZTG4 DBZTG4 DBZR DBZR	REF3 REF3 REF3 REF3 REF3 REF3 REF3	140TDD2 212AIDB' 212AIDB' 212AIDB' 220AIDB' 220AIDB' 220AIDB'	/R /T /TG4 /R /T /TG4		REF REF REF REF REF REF	3230AIDBVR 3230AIDBVT 3230AIDBVTG4 3233AIDBVR 3233AIDBVT 3233AIDBVTG4			
REF311 REF312 REF312 REF312 REF312 REF312 REF312	2AIDBZRG4 2AIDBZT 2AIDBZTG4 0AIDBZR 0AIDBZRG4 0AIDBZTG4 0AIDBZT 0AIDBZTG4 5AIDBZR	REF313 REF313 REF313 REF313 REF313 REF314 REF314	0AII 0AII 3AII 3AII 3AII 0AII	DBZRG4 DBZT DBZTG4 DBZR DBZT DBZT DBZTG4 DBZRG4 DBZR DBZRG4 DBZR DBZRG4 DBZRG4	REF3 REF3 REF3 REF3 REF3 REF3 REF3 REF3	140TDD2 212AIDB\ 212AIDB\ 212AIDB\ 220AIDB\ 220AIDB\ 220AIDB\ 220AIDB\	/R /T /TG4 /R /T /TG4 /R		REF REF REF REF REF REF	3230AIDBVR 3230AIDBVT 3230AIDBVTG4 3233AIDBVR 3233AIDBVT 3233AIDBVTG4 3240AIDBVRG4			

### **Automotive New Product Qualification Summary**

(As per AEC-Q100 and JEDEC Guidelines)

## Q100H Grade-1 qual for REF31XXAQDBZRQ1 (TSMC-WF2 / 0.5/0.6-DPDM) in HNT using 3-pin SOT pkg Approved 28-Mar-2017

## Product Attributes

Attributes	Qual Device: REF3133AQDBZRQ1	Qual Device: REF3112AQDBZRQ1	Qual Device: REF3120AQDBZRQ1	Qual Device: REF3125AQDBZRQ1	Qual Device: REF3130AQDBZRQ1	Qual Device: REF3140AQDBZRQ1	QB \$ Process Reference: OPA356AQDBVRQ1
Operating Temp Range	-40 to +125 C						
Automotive Grade Level	Grade 1						
Product Function	Power Management	Signal Chain					
Wafer Fab Supplier	TSMC-WF2						
Die Revision	E	E	E	E	E	E	-
Assembly Site	HNT	HNT	HNT	HNT	HNT	HNT	NFME
Package Type	SOT						
Package Designator	DBZ	DBZ	DBZ	DBZ	DBZ	DBZ	DBV
Ball/Lead Count	3	3	3	3	3	3	5

- QBS: Qual By Similarity
   Qual Device REF3112AQDBZRQ1 is qualified at LEVEL2-260C
   Qual Devices qualified at LEVEL3-260C: REF3120AQDBZRQ1, REF3130AQDBZRQ1, REF3140AQDBZRQ1, REF3125AQDBZRQ1, REF3133AQDBZRQ1

Qualification Results
Data Displayed as: Number of lots / Total sample size / Total failed

 Qual Device:
 Qual Device:<

PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Automotive Preconditioning	Level 2-260C peak	3/all/0	-	-	-	-	-	3/all/0
HAST	A2	A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0	-	-	-	-	-	3/231/0
AC	A3	A102	3	77	Autoclave 121C	96 Hours	3/231/0	-	-	-	-	-	3/230/0
TC	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0	-		-	-	-	3/230/0
TC-BP	A4	MIL-STD883 Method 2011	1	30	Post Temp. Cycle Bond Pull	500 Cycles	1/30/0	-	-	-	-	-	1/30/0
PTC	A5	JEDEC JESD22- A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	N/A	N/A	N/A	N/A	N/A	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temp Storage Bake 175C	500 Hours	1/45/0	-	-	-	-	-	1/45/0
Test Grou	рВ−А	ccelerated Lifetime	Simulati	on Tes	ts								
HTOL	B1	JEDEC JESD22-	3	77	Life Test, 125C	1000 Hours	3/231/0	_		_	_	-	3/231/0
ELFR	B2	A108	3	800		48 Hours	-	_	_	-	-	-	3/2400/0
EDR	B3		3	77	NIVM Endurance Data Retention		N/A	N/A	N/A	N/A	N/A	N/A	-
					and Operational Life								
Test Grow	n C _ Pa	ckane Assembly Int	enrity To	ooto									
	$\overline{}$	ickage Assembly Int		$\overline{}$									
WBS	C1	AEC Q100-001 MIL-STD883	1		Bond Shear (Cpk>1.67)	Wires	1/30/0	-	-	-	-	-	-
WBP	C2	Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	1/30/0	-	-	-	-	-	-
SD	C3	JEDEC JESD22- B102	1	15	Solderability (>95% Coverage)	Steam aging 8 hrs	-	-	-	-	-	-	1/15/0*
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	=	3/30/0	=	-	-	-	=	-
SBS	C5	AEC Q100-010	3	50	Solder Ball Shear (Cpk>1.67)	Post HTSL/Bump	NA	-	-	-	-	-	-
		JEDEC JESD22-					NA NA						
LI	C6	B105	1	50	Lead Integrity	Leads	No.	-	-	-	-	-	-
				50	Lead Integrity	Leads	No.						
		B105			Lead Integrity  Electromigration	Leads 	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group	D – Die F	B105 Fabrication Reliability T		-		Leads 	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology
Test Group EM	D – Die F	B105 Fabrication Reliability T JESD61		-	Electromigration Time Dependent Dielectric	Leads	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology
EM TDDB	D – Die F	B105 Fabrication Reliability T  JESD61  JESD35		-	Electromigration  Time Dependent Dielectric Breakdown	Leads	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements  Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology
Test Group  EM  TDDB  HCI  NBTI	D - Die F - Di	B105 B105 B105 B105 B105 B105 B105 B105	ests	-	Electromigration  Time Dependent Dielectric Break down  Hot Injection Carrier	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements  Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
EM TDDB HCI NBTI SM Test Group	D - Die F - Di	B105 abrication Reliability 1 JESD61  JESD65  JESD60 & 28  ectrical Verification	ests	-	Electromigration  Time Dependent Dielectric Breakdown  Hot Injection Carrier  Negative Bias Temperature Instability  Stress Migration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group  EM  TDDB  HCI  NBTI	D - Die F - Di	B105 B105 B105 B105 B105 B105 B105 B105	ests	-	Electromigration  Time Dependent Dielectric Breakdown  Hot Injection Carrier  Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements Completed Per Process Technology Tequirements	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements Completed Per Process Technology
EM TDDB HCI NBTI SM Test Group	D - Die F - Di	B105 abrication Reliability 1 JESD61  JESD65  JESD60 & 28  ectrical Verification	ests	3	Electromigration  Time Dependent Dielectric Breakdown  Hot Injection Carrier  Negative Bias Temperature Instability  Stress Migration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
EM TDDB HCI NBTI SM Test Group	D1 D1 D2 D3 D4 D5 E- Electron	B105 abrication Reliability J JESD61  JESD35  JESD60 & 28	ests	3 3 3 3	Electromigration  Time Dependent Dielectric Break down  Hot Injection Carrier  Negative Bias Temperature Instability  Stress Migration  ESD - HBM	2000 V 500 V (all pins)	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements
EM TDDB HCI NBTI SM Test Group HBM CDM	D1 D2 D3 D4 D5 D5 DE E E E E E S E S D E E E E E E E S	B105 abrication Reliability T JESD61  JESD65  JESD60 & 28	ests	3 3 3 6	Electromigration  Time Dependent Dielectric Breakdown  Hot Injection Carrier  Negative Bias Temperature Instability  Stress Migration  ESD - HBM  ESD - CDM		Completed Per Process Technology Requirements  100 Per Process Technology Requirements  11/3/0  11/3/0	Completed Per Process Technology Requirements  17310	Completed Per Process Technology Requirements 173/0 1/3/0	Completed Per Process Technology Requirements  173/10	Completed Per Process Technology Requirements  1/3/0	Completed Per Process Technology Requirements  173/0	Completed Per Process Technology Requirements  1/3/0

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST &TC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C

Grade 1 (or Q): -40°C to +125°C

Grade 2 (or T): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL. ED

Room/Hot/Cold: HTOL, ED Room/Hot: THB/HAST, TC/PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST
Green/Pb-free Status:
Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
WW PCN Team	PCN_www_admin_team@list.ti.com

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